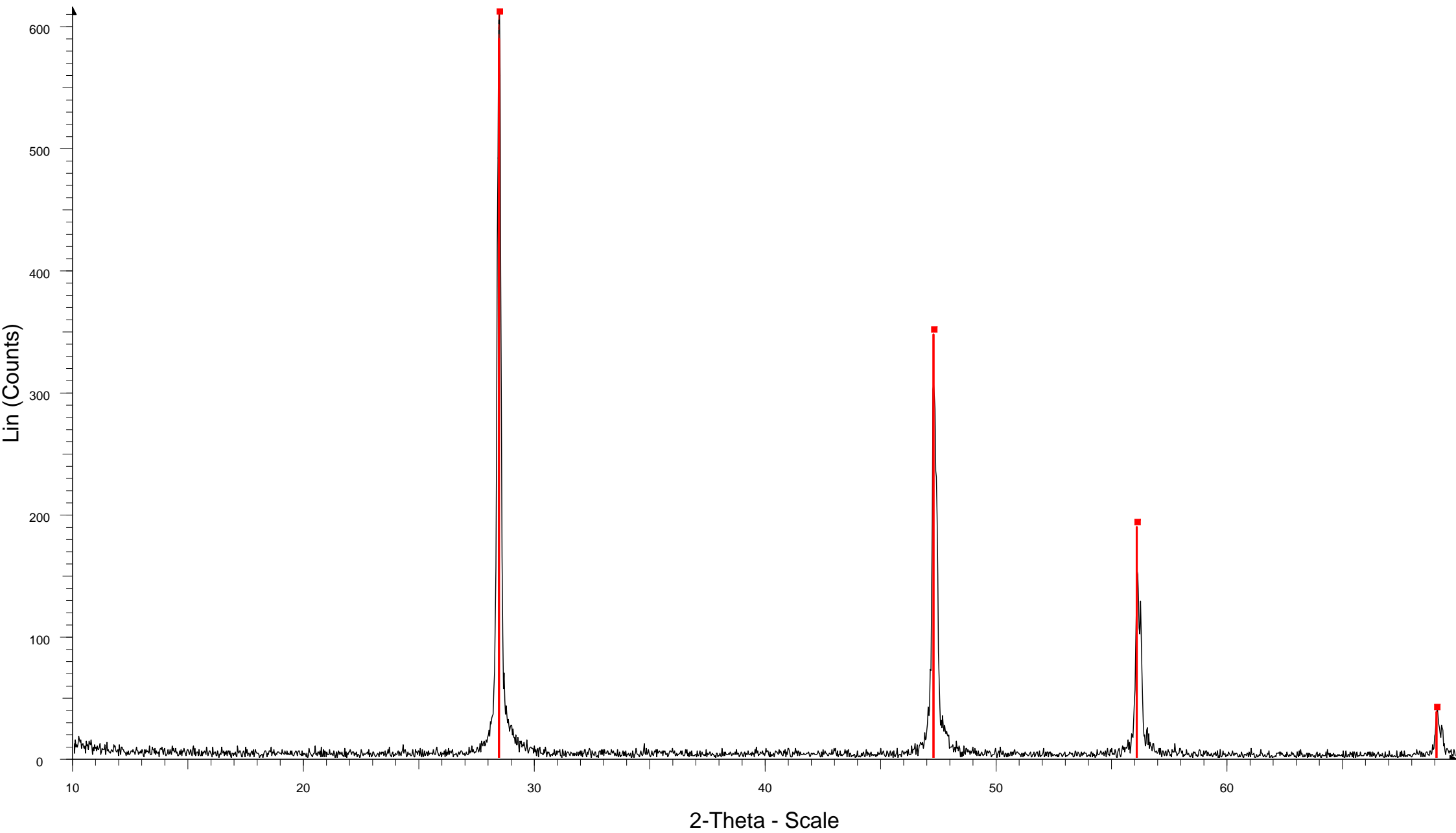


PATRÓN DE SI NIST SRM 640C 28-09-11



SI NIST XRK900 28-09-11 2 - File: SI NIST XRK900 28-09-11 2.raw - Type: 2Th/Th locked - Start: 10.000 ° - End: 69.977 ° - Step: 0.030 ° - Step time: 401. s - Temp.: 1529 °C - Time Started: 5 s - 2-Theta: 10.000 ° - Theta: 5.000 °
Operations: Import
00-027-1402 (*) - Silicon, syn - Si - Y: 100.00 % - d x by: 1. - WL: 1.5406 - Cubic - a 5.43088 - b 5.43088 - c 5.43088 - alpha 90.000 - beta 90.000 - gamma 90.000 - Face-centered - Fd-3m (227) - 8 - 160.181 - I/lc PDF 4.7 - S-Q 10

INFORME DE CALIBRACIÓN

Si NIST 640c D8C 28-09-11

Range Number : 1

R-Values

Rexp : 33.21 Rwp : 37.38 Rp : 25.17 GOF : 1.13
Rexp` : 40.20 Rwp` : 45.26 Rp` : 32.70 DW : 1.65

Instrument

Primary radius (mm) 200.5
Secondary radius (mm) 200.5
Linear PSD 2Th angular range (°) 3
 FDS angle (°) 0.6
 Beam spill, sample length (mm) 14
 Intensity not corrected
Full Axial Convolution
 Filament length (mm) 12
 Sample length (mm) 14
 Receiving Slit length (mm) 6
 Primary Sollers (°) 2.5
 Secondary Sollers (°) 4

hkl Phase - 1 Le Bail method

Phase name Silicio
 R-Bragg 2.526
 Spacegroup 227
 Cell Mass 0.000
 Cell Volume (Å³) 159.975(53)
 Wt% - Rietveld 0.000
 Crystallite Size
 Cry size Lorentzian (nm) 88.5(86)
 k: 1 LVol-IB (nm) 56.3(55)
 k: 0.89 LVol-FWHM (nm) 78.7(76)
 Strain
 Strain L 0.000(30)
 e0 0.0001(75)

Lattice parameters

a (Å) 5.42855(60)

NIST 640c Certificate

5.43311946(92)

h	k	l	m	d	Th2	I
1	1	1	8	3.13418	28.45511	5.24
0	2	2	12	1.91928	47.32477	10.1
3	1	1	24	1.63677	56.14917	7.66
2	2	2	8	1.56709	58.88465	0.14
0	0	4	6	1.35714	69.16465	3.11